

**In the claims**

1 Amend claims 1-40 where indicated.

2 1. (Withdrawn) A magnetic head assembly, which has an air bearing surface (ABS),  
3 comprising:

4 a spin valve sensor, nonmagnetic first and second read gap layers, a ferromagnetic first  
5 shield layer and a ferromagnetic first pole piece layer;

6 the spin valve sensor being located between the first and second read gap layers and the  
7 first and second read gap layers being located between the first shield layer and the first pole piece  
8 layer;

9 the spin valve sensor having a pinned layer which has a magnetic moment that is pinned  
10 by a pinning layer in a direction perpendicular to the ABS;

11 a ferromagnetic second pole piece layer and a nonmagnetic write gap layer wherein the  
12 second pole piece layer is separated from the first pole piece layer by the write gap layer at the  
13 ABS and is connected to the first pole piece layer at a back gap;

B 14 each of the first shield layer and the first and second pole piece layers having a magnetic  
15 easy axis that is directed parallel to the ABS;

16 an insulation stack with a coil layer embedded therein located between the first and second  
17 pole piece layers wherein the insulation stack includes at least one baked photoresist insulation  
18 layer that has been formed in part by heating at a preselected annealing temperature in the presence  
19 of a magnetic field that is directed perpendicular to said ABS;

20 the insulation stack having been formed subsequent to said sensor and at least the first pole  
21 piece layer having not been subjected to annealing in the presence of a magnetic field directed  
22 parallel to said ABS before said heating of the layer of the insulation stack; and

23 at least one of the first and second shield layers and the first and second pole piece layers  
24 comprising NiFeCo-O-N or NiFeCo-N.

1 2. (Withdrawn) A magnetic head assembly as described in claim 1 wherein the  
2 second shield layer and the first pole piece layer are a common layer.

1 3. (Withdrawn) A magnetic head assembly as described in claim 1 wherein the  
2 second shield layer and the first pole piece layer are separate layers and are separated by a  
3 nonmagnetic insulative isolation layer.

1 4. (Withdrawn) A magnetic head assembly as described in claim 1 wherein the  
2 second shield layer comprises NiFeCo-N.

1 5. (Withdrawn) A magnetic head assembly as described in claim 1 wherein the  
2 second pole piece layer comprises a laminated layer of NiFeCo-O-N films with interlayer films  
3 of Al<sub>2</sub>O<sub>3</sub> or SiO<sub>2</sub>.

1 6. (Withdrawn) A magnetic head assembly as described in claim 5 including:  
2 a seed layer comprising NiFeCo-O-N;  
3 the second pole piece layer being directly on the seed layer; and  
4 the seed layer having higher O and N contents than the NiFeCo-O-N of the second pole  
5 piece layer.

7. (Withdrawn) A magnetic head assembly as described in claim 6 including:  
a bottom layer of SiO<sub>2</sub>; and  
the seed layer being located between the bottom layer and the second shield layer.

1 8. (Withdrawn) A magnetic head assembly as described in claim 7 wherein the  
2 laminated layer includes four NiFeCo-O-N films that are each substantially 4500 Å thick.

1 9. (Withdrawn) A magnetic head assembly as described in claim 8 wherein the  
2 second shield layer comprises NiFeCo-N.

1 10. (Withdrawn) A magnetic disk drive including a magnetic head assembly having  
2 an air bearing surface (ABS), the disk drive comprising:  
3 the magnetic head assembly including:  
4 a spin valve sensor, first and second nonmagnetic first and second read gap layers,  
5 a ferromagnetic first shield layer and a ferromagnetic first pole piece layer;  
6 the spin valve sensor being located between the first and second read gap layers  
7 and the first and second read gap layers being located between the first shield layer and the  
8 first pole piece layer;  
9 the spin valve sensor having a pinned layer which has a magnetic moment that is  
10 pinned by a pinning layer in a direction perpendicular to the ABS;

11 a ferromagnetic second pole piece layer and a write gap layer wherein the second  
12 pole piece layer is separated from the first pole piece layer by the write gap layer at the  
13 ABS and is connected to the first pole piece layer at a back gap;  
14 each of the first shield layer and the first and second pole piece layers having an  
15 easy axis that is directed parallel to the ABS;  
16 an insulation stack with a coil layer embedded therein located between the first and  
17 second pole piece layers wherein the insulation stack includes at least one baked  
18 photoresist insulation layer that has been formed in part by heating at a preselected  
19 annealing temperature in the presence of a magnetic field that is directed perpendicular to  
20 said ABS; and  
21 the insulation stack having been formed subsequent to said sensor and at least the  
22 first pole piece layer having not been subjected to annealing in the presence of a magnetic  
23 field directed parallel to the ABS before said heating of the layer of the insulation stack;  
24 and  
25 at least one of the first and second shield layers and the first and second pole piece  
26 layers comprising NiFeCo-O-N or NiFeCo-N;  
27 a housing;  
28 a magnetic disk rotatably supported in the housing;  
29 a support mounted in the housing for supporting the magnetic head with its ABS site facing  
30 the magnetic disk so that the magnetic head is in a transducing relationship with the magnetic disk;  
31 spindle motor for rotating the magnetic disk;  
32 an actuator means connected to the support for moving the magnetic head to multiple  
33 positions with respect to said magnetic disk; and  
34 a processor connected to the magnetic head, to the spindle motor and to the actuator for  
35 exchanging signals with the magnetic head, for controlling movement of the magnetic disk and  
36 for controlling the position of the magnetic head.

1 11. (Withdrawn) A magnetic disk drive as described in claim 10 wherein the second  
2 shield layer and the first pole piece layer are a common layer.

1 12. (Withdrawn) A magnetic disk drive as described in claim 10 wherein the second  
2 shield layer and the first pole piece layer are separate layers and are separated by a nonmagnetic  
3 insulative isolation layer.

1 13. (Withdrawn) A magnetic disk drive as described in claim 10 wherein the second  
2 shield layer comprises NiFeCo-N.

1 14. (Withdrawn) A magnetic disk drive as described in claim 10 wherein the second  
2 pole piece layer comprises a laminated layer of NiFeCo-O-N films with interlayer films of  $\text{Al}_2\text{O}_3$   
3 or  $\text{SiO}_2$ .

1 15. (Withdrawn) A magnetic disk drive as described in claim 14 including:  
2 a seed layer comprising NiFeCo-O-N;  
3 the second pole piece layer being directly on the seed layer; and  
4 the seed layer having higher  $\text{O}_2$  and  $\text{N}_2$  contents than the NiFeCo-O-N of the second pole  
5 piece layer.

16. (Withdrawn) A magnetic disk drive as described in claim 15 including:  
a bottom layer of  $\text{SiO}_2$ ; and  
the seed layer being located between the bottom layer and the second shield layer.

1 17. A magnetic disk drive as described in claim 16 wherein the laminated layer includes  
2 four NiFeCo-O-N films that are each substantially 4500 Å thick.

1 18. (Withdrawn) A magnetic disk drive as described in claim 17 wherein the second  
2 shield layer comprises NiFeCo-N.

1 19. (Currently Amended) A method of making a magnetic layer with in-plane  
2 anisotropy and high  $H_K$  after hard axis annealing in the presence of a field perpendicular to the  
3 plane comprising the steps of:

4 providing a DC magnetron which has a chamber, a target and a substrate;  
5 the target being NiFeCo;

6 providing a first process gas in the chamber which is composed of an inert gas and a  
7 nitrogen containing gas; and

8 sputtering the target to form said magnetic layer composed of NiFeCo-O-N or NiFeCo-N  
9 on the substrate; and

10 hard axis annealing the magnetic layer in the presence of a magnetic field perpendicular  
11 to a major plane of the magnetic layer until the magnetic layer has an  $H_K$  from 2.6 Oe to 6.0 Oe  
12 and in-plane anisotropy.

1 20. (Original) A method as described in claim 19 wherein no bias is applied to the  
2 substrate.

1 21. (Original) A method as described in claim 19 wherein the first process gas  
2 includes 1.6% to 3.2% N<sub>2</sub>O and the magnetic layer includes multiple sputtered NiFeCo-O-N or  
3 NiFeCo-N films.

1 22. (Original) A method as described in claim 19 wherein the first process gas  
2 includes 1.6% to 3.2% N<sub>2</sub>O and the magnetic layer is a single film 2,500 Å to 6,000 Å thick.

1 23. (Original) A method as described in claim 19 wherein the first process gas  
2 includes 1.0% to 2.0% N<sub>2</sub> and the magnetic layer is a single film 4,500 Å to 18,000 Å thick.

1 24. (Original) A method as described in claim 19 wherein the target is (Ni<sub>0.80+</sub>  
2 <sub>x</sub>Fe<sub>0.20-x</sub>)<sub>1-y</sub>Co<sub>y</sub> where -0.05 ≤ x ≤ 0.05 and 0.00 ≤ y ≤ 0.15 (wt. fraction).  
3

1 25. (Original) A method as described in claim 19 wherein the first process gas is  
2 said inert gas and N<sub>2</sub> and the target is sputtered to form the magnetic layer of at least a single film  
3 of NiFeCo-N about 1.8 μm thick.

1 26. (Original) A method as described in claim 25 wherein the first process gas  
2 includes 1.0% to 2.0% N<sub>2</sub>.

1 27. (Currently Amended) A method as described in claim 26 wherein during  
2 sputtering the first target, a pressure between 1 x 10<sup>-3</sup> to 3 x 10<sup>-3</sup> mbar is maintained within said  
3 chamber and the magnetic layer comprises one or more films of NiFeCo-N from 4,500 Å to  
4 18,000 Å thick.

1 28. (Original) A method as described in claim 19 including:  
2 the first process gas being said inert gas and N<sub>2</sub>O;  
3 sputter depositing multiple interlayer films of Al<sub>2</sub>O<sub>3</sub> or SiO<sub>2</sub>; and  
4 sputtering the target multiple times to deposit multiple NiFeCo-O-N magnetic films;  
5 and alternating the depositions to form the magnetic layer as a lamination of magnetic and  
6 interlayer films.

1           29.     (Currently Amended) ~~A method as described in claim 28 including:~~ A method  
2 of making a magnetic layer with in-plane anisotropy and high  $H_K$  after hard axis annealing in the  
3 presence of a field perpendicular to the plane comprising the steps of:

4           providing a DC magnetron which has a chamber, a target and a substrate;  
5           the target being NiFeCo;

6           providing a first process gas in the chamber which is composed of an inert gas and  $N_2O$ ;  
7           sputtering the target to form said magnetic layer composed of NiFeCo-O-N or NiFeCo-N  
8 on the substrate;

9           sputter depositing multiple interlayer films of  $Al_2O_3$  or  $SiO_2$ ;  
10           sputtering the target multiple times to deposit multiple NiFeCo-O-N magnetic films;  
11           alternating the depositions to form the magnetic layer as a lamination of magnetic and  
12 interlayer films;

13           hard axis annealing the magnetic layer at about 232° C in the presence of magnetic field  
14 perpendicular to a major plane of the magnetic layer for about 400 minutes; and

15           after said hard axis annealing, the magnetic layer having an  $H_K$  from 2.6 Oe to 6.0 Oe and  
16 in plane anisotropy.

B  
1           30.     (Original)     A method as described in claim 28 wherein the first process gas  
2 includes 1.6% to 3.2%  $N_2O$  and each of the NiFeCo-O-N films is about 4,500 Å thick.

1           31.     (Original)     A method as described in claim 28 wherein no bias is applied to the  
2 substrate.

1           32.     (Currently Amended) ~~A method as described in claim 28 wherein~~ A method of  
2 making a magnetic layer with in-plane anisotropy and high  $H_K$  after hard axis annealing in the  
3 presence of a field perpendicular to the plane comprising the steps of:

4           providing a DC magnetron which has a chamber, a target and a substrate;  
5           the target being NiFeCo;

6           providing a first process gas in the chamber which is composed of an inert gas and  $N_2O$ ;  
7           sputtering the target to form said magnetic layer composed of NiFeCo-O-N or NiFeCo-N  
8 on the substrate;

9           before sputtering the target, sputter depositing a seed layer of NiFeCo-O-N with a second  
10 process gas that has a higher  $N_2O$  content than the first process gas;

11 sputter depositing multiple interlayer films of  $\text{Al}_2\text{O}_3$  or  $\text{SiO}_2$ ;  
12 sputtering the target multiple times to deposit multiple NiFeCo-O-N magnetic films; and  
13 alternating the depositions to form the magnetic layer as a lamination of magnetic and  
14 interlayer films.

1 33. (Original) A method as described in claim 32 wherein the seed layer is 25 Å  
2 to 200 Å thick.

1 34. (Original) A method as described in claim 32 including:  
2 before sputter depositing the seed layer, sputter depositing a bottom layer of  $\text{SiO}_2$  so that  
3 the seed layer is located between the bottom layer and the magnetic layer.

1 35. (Original) A method as described in claim 32 wherein the  $\text{N}_2\text{O}$  content in the  
2 second process gas is from 2.4% to 4.0%.

1 36. (Original) A method as described in claim 35 wherein no bias is applied to the  
2 substrate.

1 37. (Original) A method as described in claim 36 including:  
2 before sputter depositing the seed layer, sputter depositing a bottom layer of  $\text{SiO}_2$  so that  
3 the seed layer is located between the bottom layer and the magnetic layer.

1 38. (Original) A method as described in claim 37 wherein the seed layer is 25 Å  
2 to 200 Å thick.

1 39. (Original) A method as described in claim 38 wherein the bottom layer is about  
2 25 Å thick.

1 40. (Original) A method as described in claim 39 wherein four NiFeCo-O-N  
2 magnetic films are deposited with each magnetic film being about 4500 Å thick and each  
3 interlayer film being about 25 Å thick.